

**TF3407** P-Channel 30-V(D-S) MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	$I_D$
-30V	0.050Ω@-10V	-4.1A
	0.070Ω@-4.5V	

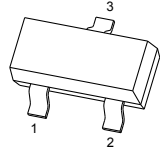
**General FEATURE**

- TrenchFET Power MOSFET
- Lead free product is acquired
- Surface mount package

**APPLICATION**

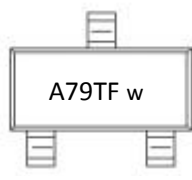
- Load Switch for Portable Devices
- DC/DC Converter

**SOT-23-3L**



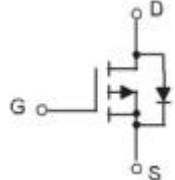
1.GATE  
2.SOURCE  
3.DRAIN

**MARKING**



\*w: week code

**Equivalent Circuit**



**Maximum ratings (T<sub>a</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	±20	
Continuous Drain Current	$I_D$	-4.1	A
Pulsed Drain Current	$I_{DM}$	-20	
Maximum Power Dissipation	$P_D$	1.4	W
Thermal Resistance from Junction to Ambient(t ≤5s)	$R_{\theta JA}$	84	°C/W
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{stg}$	-55 ~+150	



# SOT-23-3L Plastic-Encapsulate MOSFETS

TF3407

## MOSFET ELECTRICAL CHARACTERISTICS

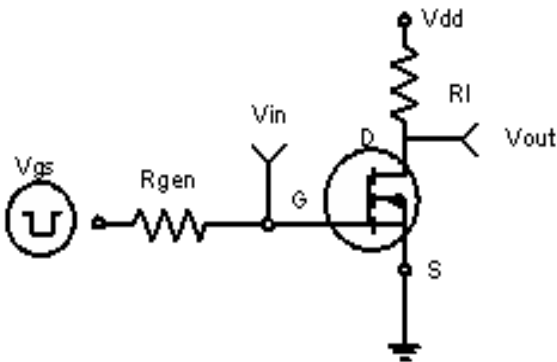
T<sub>a</sub> =25 °C unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Static characteristics</b>						
Drain-source breakdown voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	-30			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V			-1	μA
Gate-source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±100	nA
Drain-source on-resistance (note a)	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -4.1A		48	50	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3A		65	70	mΩ
Forward tranconductance (note a)	g <sub>FS</sub>	V <sub>DS</sub> = -5V, I <sub>D</sub> = -4.1A	5.5			S
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-1	-1.4	-3	V
Diode forward voltage (note a)	V <sub>SD</sub>	I <sub>S</sub> = -1A, V <sub>GS</sub> = 0V			-1	V
<b>Dynamic characteristics (note b)</b>						
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1MHz		700		pF
Output capacitance	C <sub>oss</sub>			120		pF
Reverse transfer capacitance	C <sub>rss</sub>			75		pF
<b>Switching Characteristics (note b)</b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>GS</sub> = -10V, V <sub>DS</sub> = -15V, R <sub>L</sub> = 3.6Ω, R <sub>GEN</sub> = 3Ω		9.0		ns
Turn-on rise time	t <sub>r</sub>			5.0		ns
Turn-off delay time	t <sub>d(off)</sub>			28.2		ns
Turn-off fall time	t <sub>f</sub>			13.5		ns

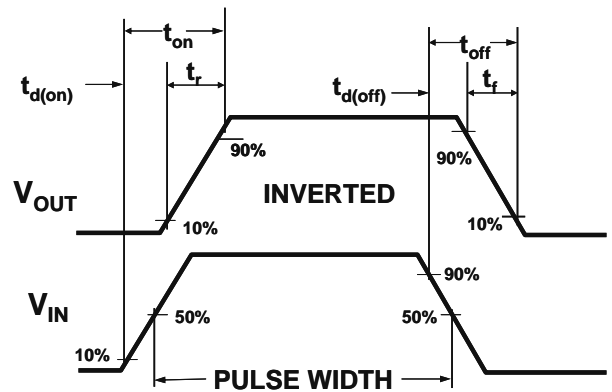
**Notes:**

- a. Pulse Test : Pulse Width < 300μs, Duty Cycle ≤2%.
- b. These parameters have no way to verify.

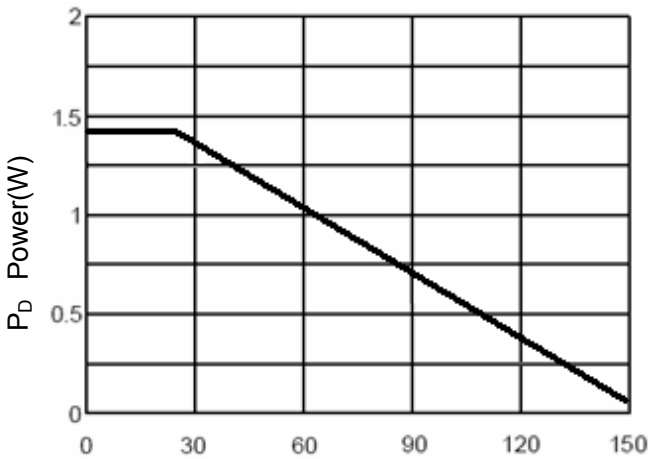
**Typical Electrical and Thermal Characteristics**



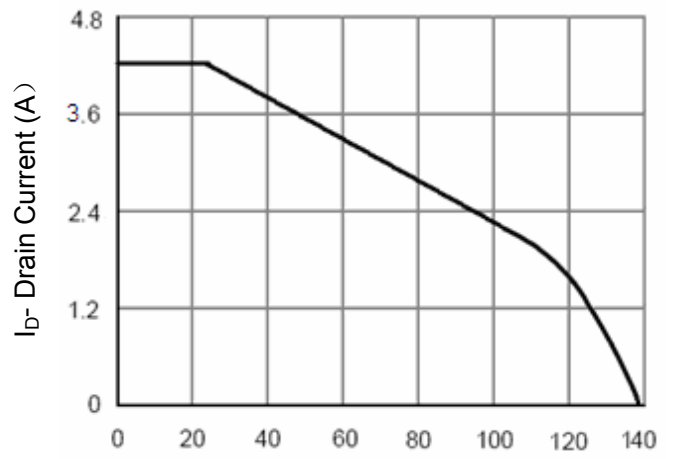
**Figure 1: Switching Test Circuit**



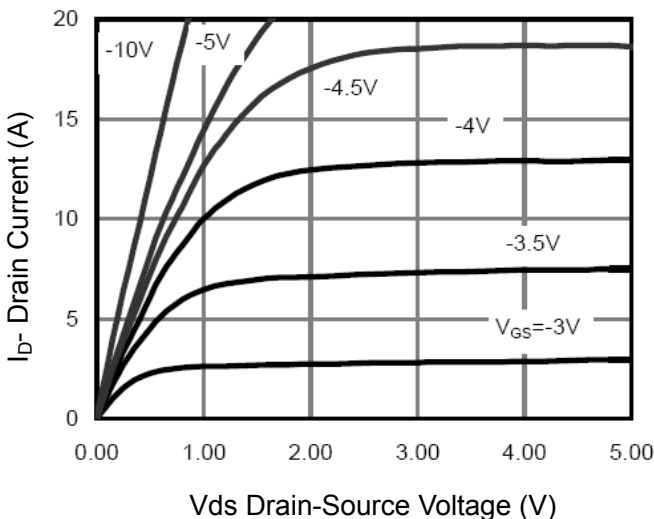
**Figure 2: Switching Waveforms**



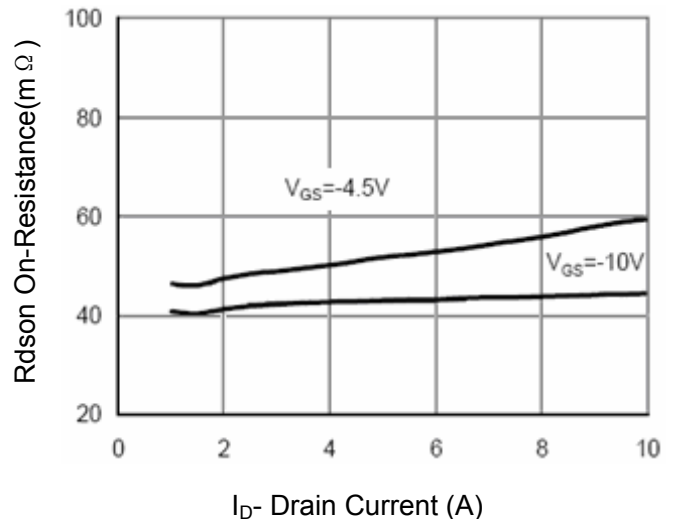
**Figure 3 Power Dissipation**



**Figure 4 Drain Current**



**Figure 5 Output Characteristics**



**Figure 6 Drain-Source On-Resistance**

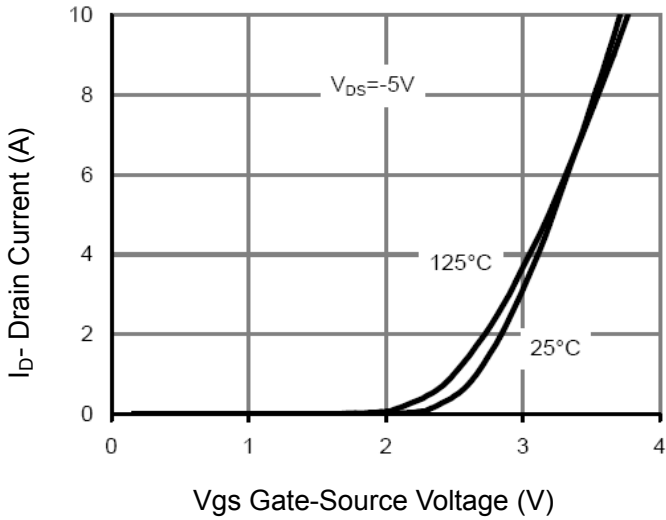


Figure 7 Transfer Characteristics

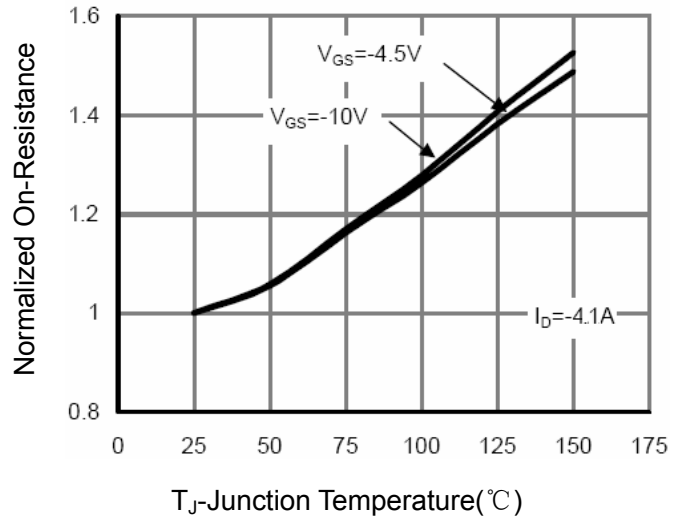


Figure 8 Drain-Source On-Resistance

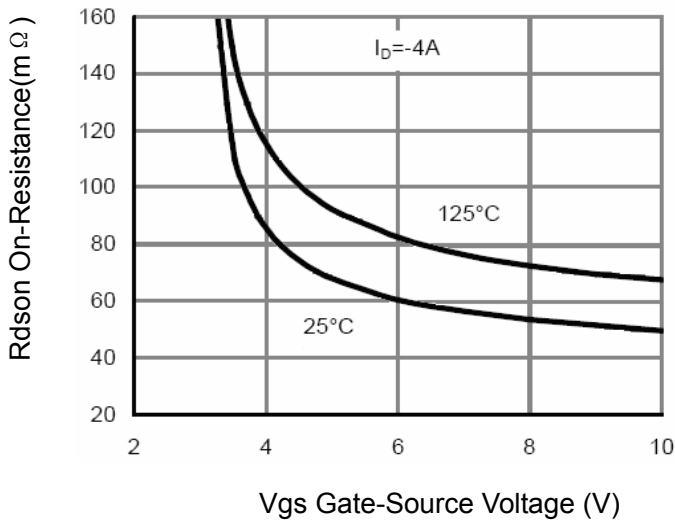


Figure 9 Rdson vs Vgs

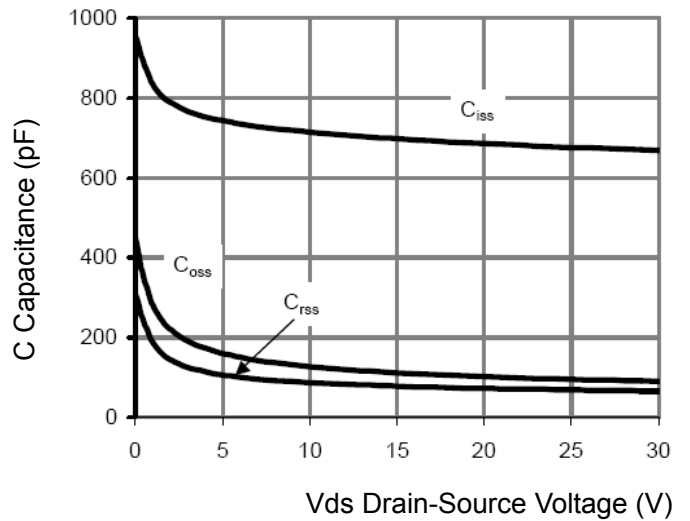


Figure 10 Capacitance vs Vds

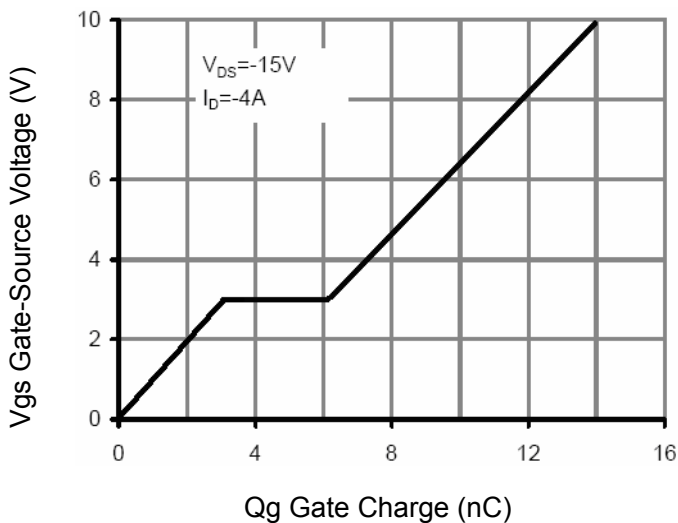


Figure 11 Gate Charge

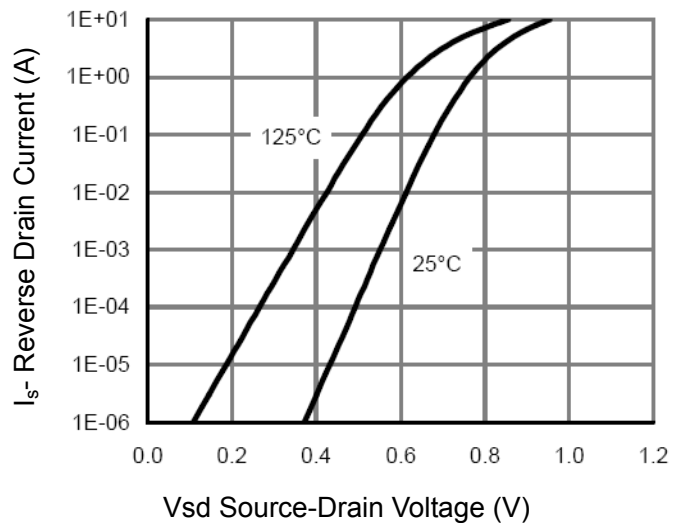


Figure 12 Source- Drain Diode Forward

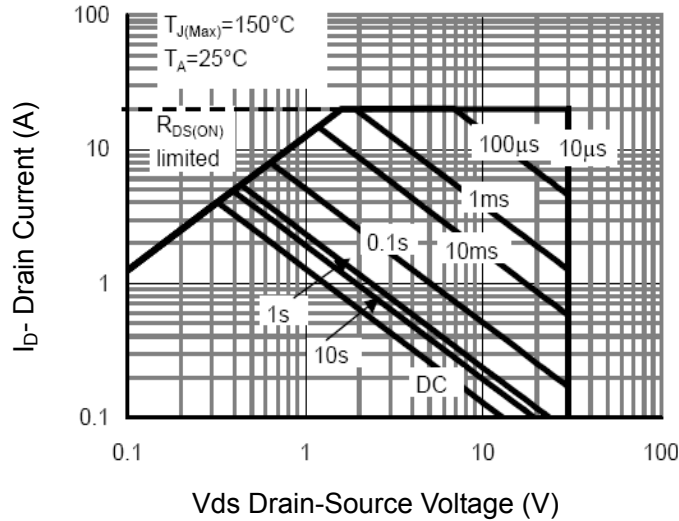


Figure 13 Safe Operation Area

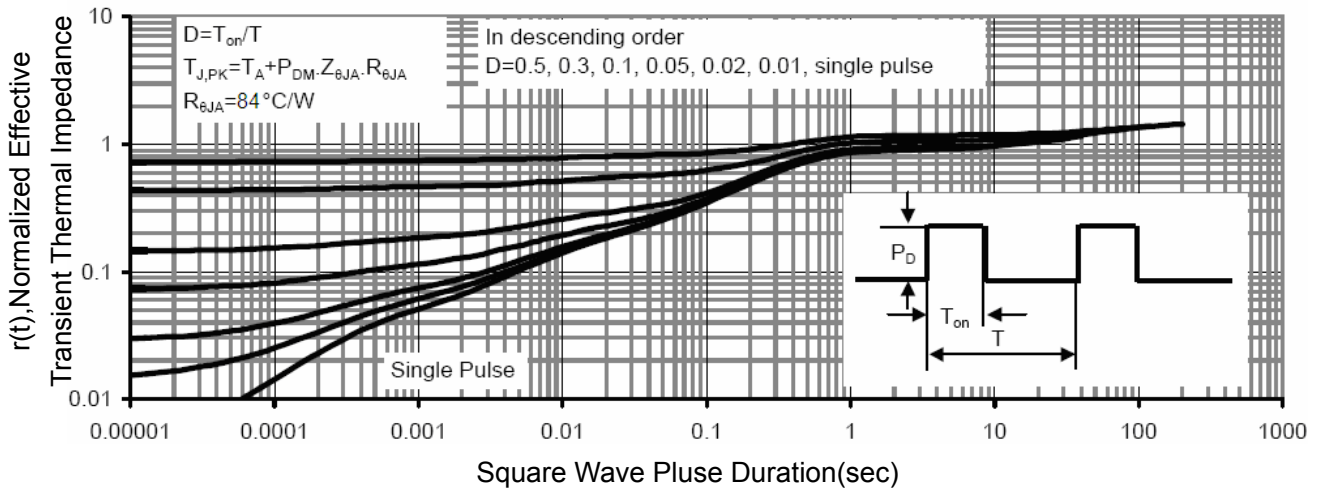
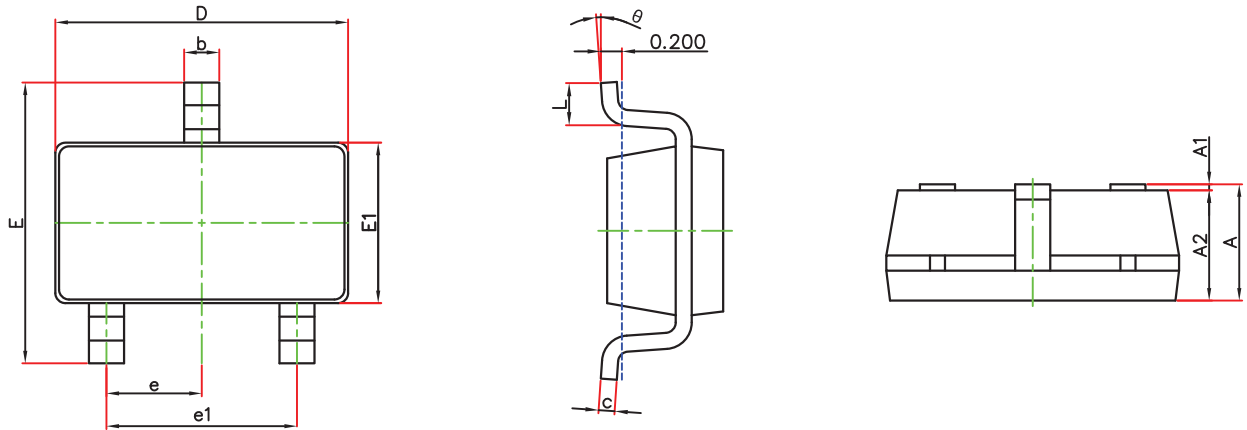


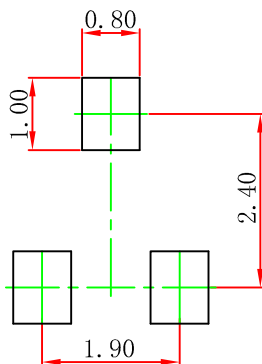
Figure 14 Normalized Maximum Transient Thermal Impedance

**SOT-23-3L Package Outline Dimensions**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

**SOT-23-3L Suggested Pad Layout**



- Note:
1. Controlling dimension: in millimeters.
  2. General tolerance:  $\pm 0.05\text{mm}$ .
  3. The pad layout is for reference purposes only.